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PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

HiroYuki KIYOKU *et al.*

Appln. No.: Continuation of 09/603,437

Group Art Unit: 1765

Confirmation No.: To be Assigned

Examiner: To be Assigned

Filed:

For: NITRIDE SEMICONDUCTOR GROWTH METHOD, SEMICONDUCTOR
SUBSTRATE, AND NITRIDE SEMICONDUCTOR DEVICE

PRELIMINARY AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

Sir:

Prior to examination, please amend the above-identified application as follows:

IN THE SPECIFICATION:

Before the first line of the specification, please insert the following new paragraph:

This is a Continuation of application Serial No. 09/603,437 filed June 23, 2000, now pending, which is a Division of application Serial No. 09/202,141 filed December 9, 1998, now U.S. Patent 6,153,010, which is a 35 U.S.C. § 371 of PCT/JP98/01640 filed April 9, 1998.

Page 5, please delete the first full paragraph, and replace it with the following new paragraph:

In the first and second aspects of the present invention, the first selective growth mask is preferably made up of a plurality of individual or discrete stripes spaced apart from each other,